

Vishay Siliconix

Low-Leakage Pico-Amp Diodes

PAD1 JPAD5 SSTPAD5 PAD5 JPAD50 SSTPAD100 PAD50

PRODUCT SUMMARY					
Part Number	I _R Max (pA)				
PAD1	-1				
PAD5/JPAD5/SSTPAD5	- 5				
PAD50/JPAD50	-50				
SSTPAD100	-100				

FEATURES

- Ultralow Leakage: PAD1 <1 pA
- Ultralow Capacitance: PAD1 <0.8 pF
- Two-Leaded Package

BENEFITS

- Negligible Circuit Leakage Contribution
- Circuit "Transparent" Except to Shunt High-Frequency Spikes
- Simplicity of Operation

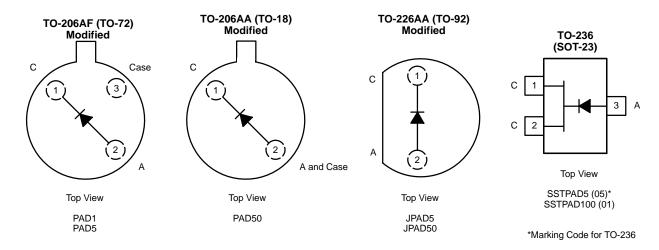
APPLICATIONS

- Op Amp Input Protection
- Multiplexer Overvoltage Protection

DESCRIPTION

The PAD/JPAD/SSTPAD series of extremely low-leakage diodes provides a superior alternative to conventional diode technology when reverse current (leakage) must be minimized. They feature leakage currents ranging from -1 pA (PAD1) to -100 pA (SSTPAD100) to support a wide range of applications. These devices are well suited for use in applications such as input protection for operational amplifiers.

The hermetically sealed TO-206AF (TO-72) package allows full military processing per MIL-S-19500 (see Military Information). The TO-226A (TO-92) plastic package provides a low-cost option. The TO-236 (SOT-23) package provides surface-mount capability. Both J and SST series are available in tape-and-reel for automated assembly. (See Packaging Information.)



PAD/JPAD/SSTPAD Series

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ABSOLUTE MAXIMUM RATINGS^a

(JPAD/SSTPAD)
Total Device Dissipation: (PAD)b
(JPAD/SSTPAD)b 350 mW
Operation Junction Temp: (PAD)
(JPAD/SSTPAD)°55 to 150°C
Lead Temperature (1/16" from case for 10 sec.)

Notes:

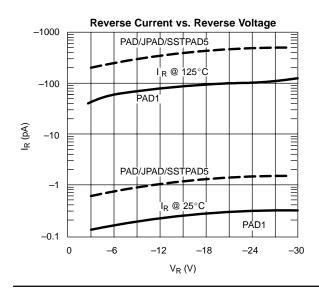
- $T_A = 25$ °C unless otherwise noted. a. Derate 2 mW/°C above 25°C.

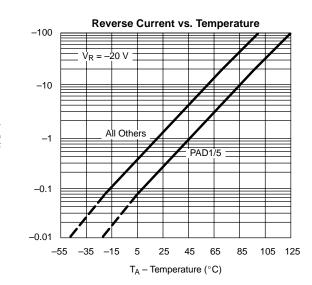
 Derate 2.8 mW/°C above 25°C.

SPECIFICATIONS SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)									
		Test Conditions		Limits					
Parameter	Symbol			Min	Typ ^a	Max	Unit		
Static									
Reverse Current	I _R	V _R = -20 V	PAD1		-0.3	-1	pA		
			PAD5/JPAD5/SSTPAD5		-1	- 5			
			PAD50/JPAD50		-5	-50			
			SSTPAD100		-10	-100			
Reverse Breakdown Voltage	BV _R	I _R = -1 μΑ	PAD1/PAD5	-45	-60				
			SSTPAD5/100	-30	-55				
			All Others	-35	-55		V		
Forward Voltage Drop	V _F	I _F = 1 mA			0.8	1.5	1		
Dynamic									
Reverse Capacitance	C _R	V _R = −5V, f = 1 MHz	PAD1/PAD5		0.5	0.8	pF		
			All Others		1.5	2			

Notes:

TYPICAL CHARACTERISTICS (TA = 25°C UNLESS OTHERWISE NOTED)





a. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.



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